

# SOT-227 Silicon Carbide Schottky Barrier Diode, 650 V, 40 A



SOT-227


RoHS  
COMPLIANT

## FEATURES

- Virtually no recovery tail and no switching losses
- Majority carrier diode using Schottky technology on SiC wide band gap material
- Improved  $V_F$  and efficiency by thin wafer technology
- High speed switching, low switching losses
- Positive temperature coefficient, for easy paralleling
- Electrically isolated base plate
- Large creepage distance between terminal
- Simplified mechanical designs, rapid assembly
- Designed and qualified for industrial level
- UL approved file E78996 
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

## DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters

| PRIMARY CHARACTERISTICS                             |                                       |
|-----------------------------------------------------|---------------------------------------|
| $V_R$                                               | 650 V                                 |
| $V_F$ (typical) at 20 A, per diode                  | 1.36 V                                |
| $Q_C$ (typical), per diode                          | 56 nC                                 |
| $I_{F(DC)}$ per module at $T_C = 136^\circ\text{C}$ | 40 A                                  |
| Type                                                | Modules - diode, SiC Schottky         |
| Package                                             | SOT-227                               |
| Circuit configuration                               | Two separate diodes, parallel pin-out |

| ABSOLUTE MAXIMUM RATINGS                         |                |                                              |             |                  |
|--------------------------------------------------|----------------|----------------------------------------------|-------------|------------------|
| PARAMETER                                        | SYMBOL         | TEST CONDITIONS                              | MAX.        | UNITS            |
| Cathode to anode voltage                         | $V_R$          |                                              | 650         | V                |
| Continuous forward current per diode             | $I_F$          | $T_C = 136^\circ\text{C}$                    | 20          | A                |
| Single pulse forward current per diode           | $I_{FSM}$      | $T_J = 25^\circ\text{C}$ , 6 ms square pulse | 105         |                  |
| Maximum power dissipation per module             | $P_D$          | $T_C = 136^\circ\text{C}$                    | 74          | W                |
| RMS isolation voltage                            | $V_{ISOL}$     | Any terminal to case, $t = 1$ min            | 2500        | V                |
| Operating junction and storage temperature range | $T_J, T_{Stg}$ |                                              | -55 to +175 | $^\circ\text{C}$ |

| ELECTRICAL SPECIFICATIONS ( $T_J = 25^\circ\text{C}$ unless otherwise specified) |          |                                                   |      |      |      |               |
|----------------------------------------------------------------------------------|----------|---------------------------------------------------|------|------|------|---------------|
| PARAMETER                                                                        | SYMBOL   | TEST CONDITIONS                                   | MIN. | TYP. | MAX. | UNITS         |
| Cathode to anode breakdown voltage                                               | $V_{BR}$ | $I_R = 100\ \mu\text{A}$                          | 650  | -    | -    | V             |
| Forward voltage                                                                  | $V_{FM}$ | $I_F = 20\ \text{A}$                              | -    | 1.36 | 1.55 |               |
|                                                                                  |          | $I_F = 20\ \text{A}$ , $T_J = 150^\circ\text{C}$  | -    | 1.57 | -    |               |
| Reverse leakage current                                                          | $I_{RM}$ | $V_R = 650\ \text{V}$                             | -    | 1    | 40   | $\mu\text{A}$ |
|                                                                                  |          | $T_J = 125^\circ\text{C}$ , $V_R = 650\ \text{V}$ | -    | 3.1  | -    |               |
|                                                                                  |          | $T_J = 150^\circ\text{C}$ , $V_R = 650\ \text{V}$ | -    | 4.6  | -    |               |
| Junction capacitance                                                             | $C_T$    | $V_R = 650\ \text{V}$ , $f = 1\ \text{MHz}$       | -    | 82   | -    | pF            |

**DYNAMIC RECOVERY CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

| PARAMETER               | SYMBOL | TEST CONDITIONS      | MIN. | TYP. | MAX. | UNITS |
|-------------------------|--------|----------------------|------|------|------|-------|
| Total capacitive charge | $Q_C$  | $V_R = 400\text{ V}$ | -    | 56   | -    | nC    |

**THERMAL - MECHANICAL SPECIFICATIONS**

| PARAMETER                                       | SYMBOL     | TEST CONDITIONS       | MIN.    | TYP. | MAX.       | UNITS              |
|-------------------------------------------------|------------|-----------------------|---------|------|------------|--------------------|
| Thermal resistance junction to case, per diode  | $R_{thJC}$ |                       | -       | -    | 1.06       | $^\circ\text{C/W}$ |
| Thermal resistance junction to case, per module |            |                       | -       | -    | 0.53       |                    |
| Thermal resistance case to heatsink, per module | $R_{thCS}$ | Flat, greased surface | -       | 0.05 | -          |                    |
| Weight                                          |            |                       | -       | 30   | -          | g                  |
| Mounting torque                                 |            | Torque per diode      | -       | -    | 1.1 (9.7)  | Nm (lbf.in)        |
|                                                 |            | Torque to heatsink    | -       | -    | 1.8 (15.9) | Nm (lbf.in)        |
| Case style                                      |            |                       | SOT-227 |      |            |                    |

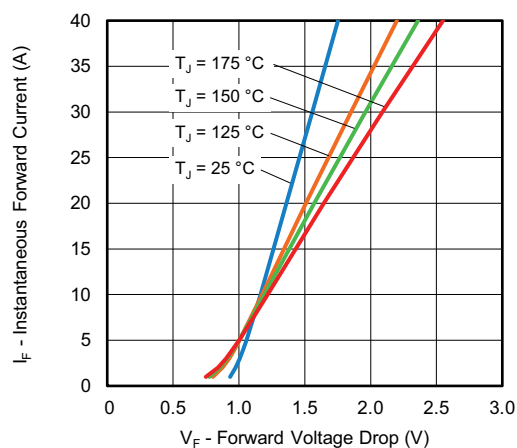


Fig. 1 - Typical Forward Voltage Drop Characteristics

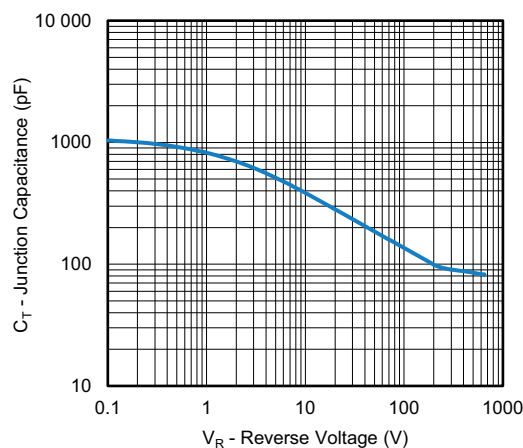


Fig. 3 - Junction Capacitance vs. Reverse Voltage

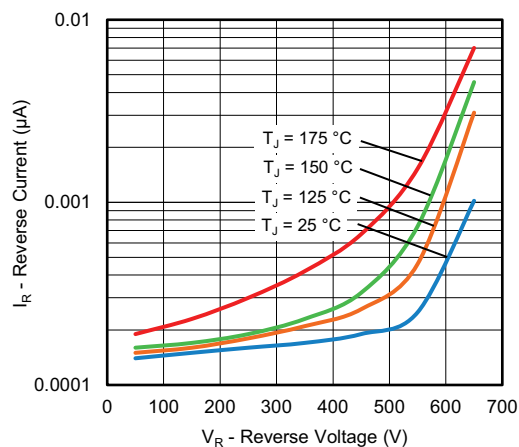


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

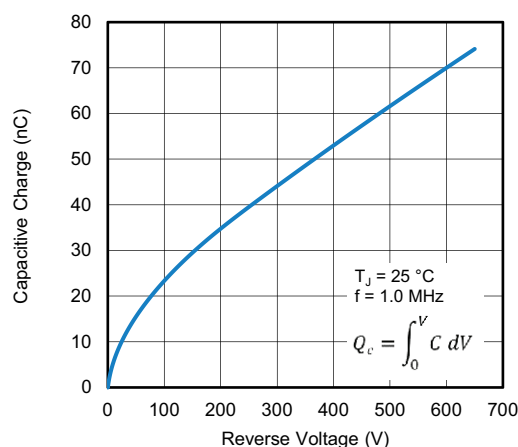


Fig. 4 - Typical Capacitive Charge vs. Reverse Voltage

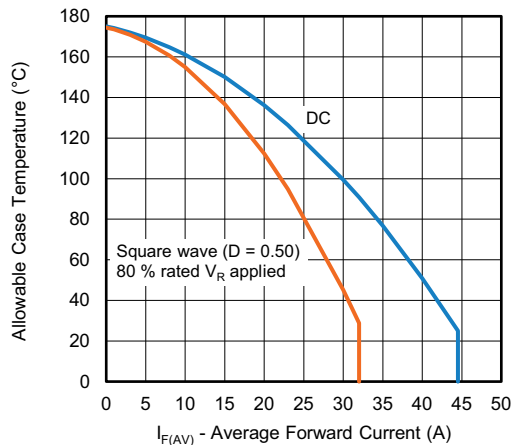


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

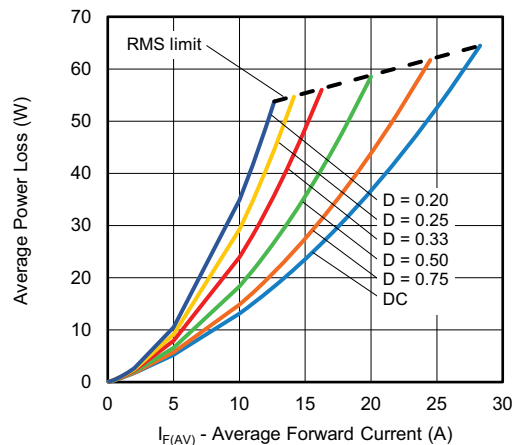


Fig. 6 - Forward Power Loss Characteristics

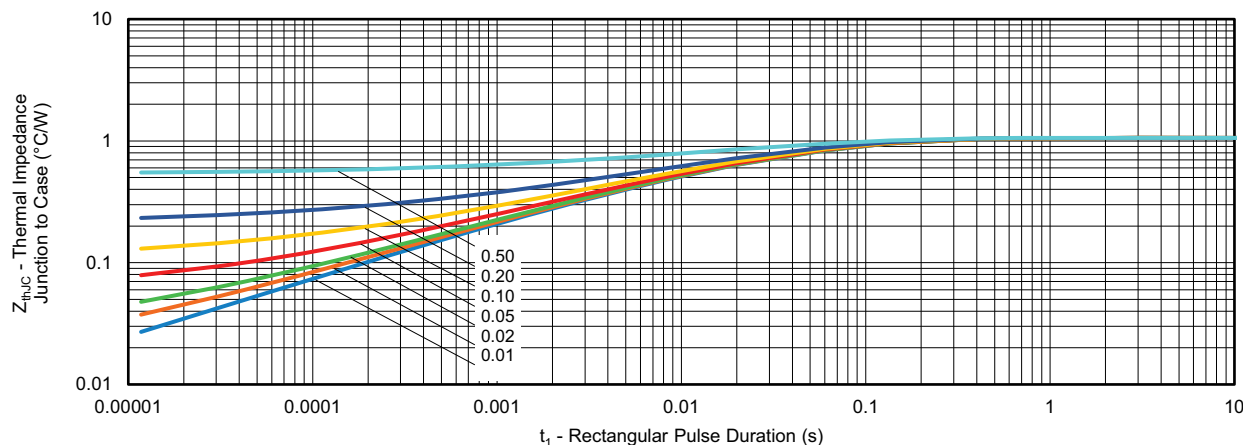


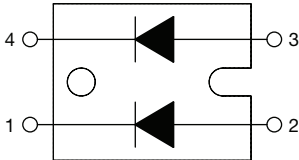
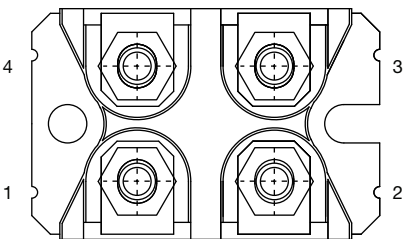
Fig. 7 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

## ORDERING INFORMATION TABLE

| Device code | VS- | SC | 40 | F | A | 65 |
|-------------|-----|----|----|---|---|----|
|             | ①   | ②  | ③  | ④ | ⑤ | ⑥  |

- 1** - Vishay Semiconductors product
- 2** - SC = SiC Schottky Barrier Diode
- 3** - Current rating per module (40 = 40 A)
- 4** - F = circuit configuration (two separate diodes, parallel pin-out)
- 5** - Package indicator (SOT-227 standard insulated base)
- 6** - Voltage rating (65 = 650 V)

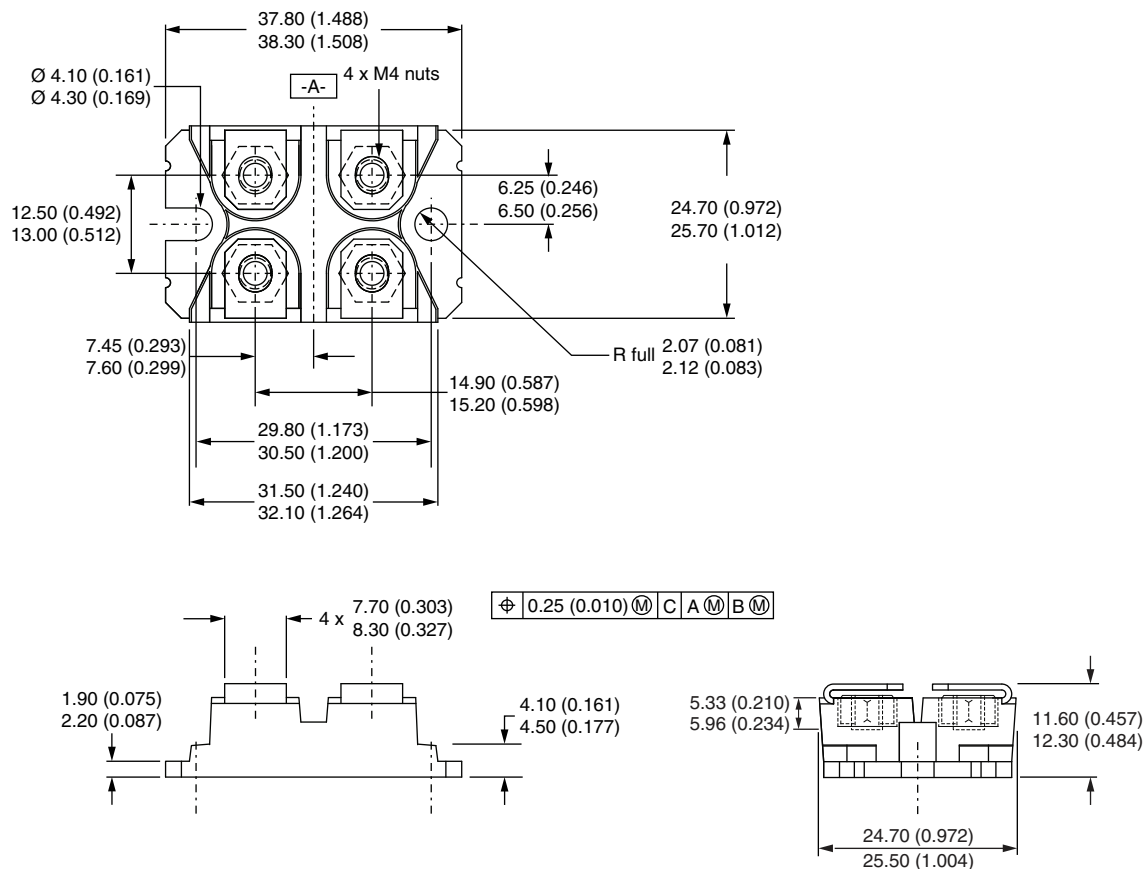


| CIRCUIT CONFIGURATION                 |                            |                                                                                                                                                                                                                             |
|---------------------------------------|----------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| CIRCUIT                               | CIRCUIT CONFIGURATION CODE | CIRCUIT DRAWING                                                                                                                                                                                                             |
| Two separate diodes, parallel pin-out | F                          | <div><div></div><div><p>Lead Assignment</p></div></div> |

| LINKS TO RELATED DOCUMENTS |                                                                        |
|----------------------------|------------------------------------------------------------------------|
| Dimensions                 | <a href="http://www.vishay.com/doc?95423">www.vishay.com/doc?95423</a> |
| Packaging information      | <a href="http://www.vishay.com/doc?95425">www.vishay.com/doc?95425</a> |

## SOT-227 Generation 2

**DIMENSIONS** in millimeters (inches)



### Note

- Controlling dimension: millimeter



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